TXB0104 4 ビット双方向電圧レベル・トランスレータ、自動方向検出機能および±15kV ESD 保護付き

1 特長

- A ポートで 1.2V～3.6V、B ポートで 1.65V～5.5V ($V_{CCA} \leq V_{CCB}$)
- V_{CC} 絶縁機能: どちらかの V_{CC} 入力が GND レベルになると、すべての出力がハイ・インピーダンス状態になる
- V_{CCA} を基準とする出力イネーブル (OE) 入力回路
- 低い消費電力、最大 I_{CC}:5μA
- I_{OFF} により部分的パワーダウン・モードをサポート
- JESD 78, Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 を超える ESD 保護
  - A ポート:
    - 2500V、人体モデル (A114-B)
    - 1500V、デバイス帯電モデル (C101)
  - B ポート:
    - ±15kV、人体モデル (A114-B)
    - 1500V、デバイス帯電モデル (C101)

2 アプリケーション

- ヘッドセット
- スマートフォン
- タブレット
- デスクトップ PC

3 概要

この TXB0104 4 ビット非反転トランスレータは、設定可能な 2 本の独立した電源レールを採用しています。A ポートは V_{CCA} に追従する設計で、V_{CCA} には 1.2V～3.6V の電源電圧を供給できます。B ポートは V_{CCB} に追従する設計で、V_{CCB} には 1.65V～5.5V の電源電圧を供給できます。このため 1.2V、1.5V、1.8V、2.5V、3.3V、5V のいずれかの電圧ノード間で、低電圧の双方向変換を自在に行うことが可能になります。V_{CCA} が V_{CCB} を上回ることはできません。

OE 入力が Low のとき、全出力がハイ・インピーダンス状態になります。電源投入時または切断時にハイ・インピーダンス状態を確保するには、OE をプルダウン抵抗で GND につなぐ必要があります。この抵抗の最小値は、ドライバの電流ソース能力によって決まります。

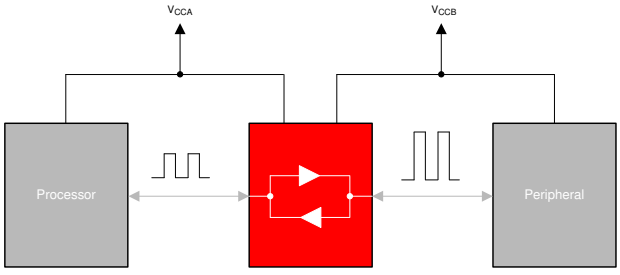
TXB0104 は、OE 入力回路が V_{CCA} によって給電されるように設計されています。

このデバイスは、I_{OFF} を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。I_{OFF} 回路が出力をディセーブルにするするため、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。

製品情報

(1)部品番号	パッケージ	本体サイズ (公称)
TXB0104RUT	UQFN (12)	2.00mm × 1.70mm
TXB0104D	SOIC (14)	8.65mm × 3.91mm
TXB0104ZXU/GXU	BGA MICROSTAR JUNIOR™ (12)	2.00mm × 2.50mm
TXB0104PW	TSSOP (14)	5.00mm × 4.40mm
TXB0104RGY	VQFN (14)	3.50mm × 3.50mm
TXB0104YZT	DSBGA (12)	1.40mm × 1.90mm
TXB0104NMN	NFBGA (12)	2.00mm × 2.50mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



TXB0108 の代表的なアプリケーション・ブロック図

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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision I (March 2018) to Revision J (October 2020) — **Page**

- 文書全体にわたって表、図、相互参照の採番方法を更新 ... 1
- Added NMN Package, 12-Pin NFBGA pinout drawing in *Pin Configuration and Functions* section ... 3

Changes from Revision H (January 2018) to Revision I (March 2018) — **Page**

- Updated *Pin Functions* table ... 3
- Added *Pin Assignments* table for YZT package ... 3
- Added *Pin Assignments* table for GXU and ZXU package ... 3
- Updated *Layout Example* ... 22

Changes from Revision G (November 2014) to Revision H (January 2018) — **Page**

- Added Package, families to Package, pinout drawings in *Pin Configuration and Functions* section ... 3
- Added junction temperature range in *Absolute Maximum Ratings*table ... 5
- Changed unit from V to kV in *ESD Ratings* table ... 5

Changes from Revision F (May 2012) to Revision G (November 2014) — **Page**

- 「ピン構成および機能」セクション、「取り扱いに関する定格」の表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加 ... 1

5 Pin Configuration and Functions

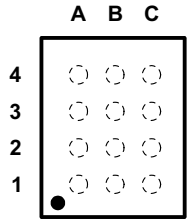


図 5-1. GXU and ZXU Package, 12-Pin BGA Microstar Junior (Top View)

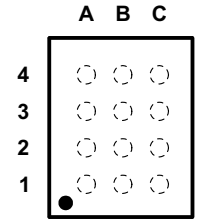


図 5-2. NMN Package, 12-Pin NFBGA (Top View)

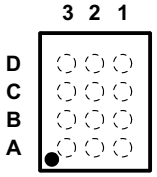
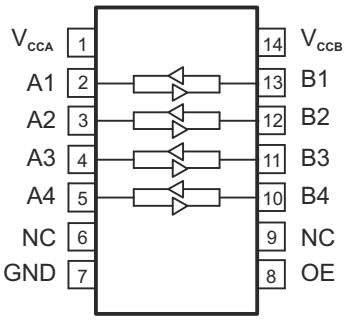
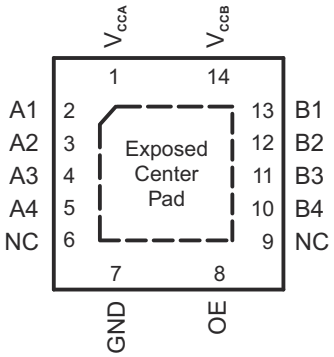


図 5-3. YZT Package, 12-Pin DSBGA (Top View)



NC − No internal connection

図 5-4. D or PW Package, 14-Pin SOIC or TSSOP (Top View)



NC − No internal connection

図 5-5. RGY Package, 14-Pin VQFN With Exposed Thermal Pad (Top View)

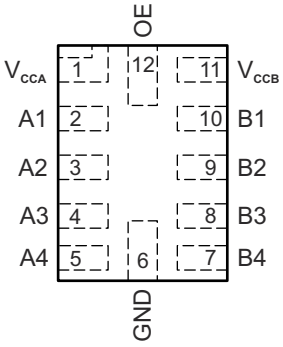


図 5-6. RUT Package, 12-Pin UQFN (Top View)

表 5-1. Pin Functions

PIN						I/O	DESCRIPTION
NAME	D, PW	RGY	RUT	GXU, ZXU, NMN	YZT		
A1	2	2	2	A1	A3	I/O	Input/output 1. Referenced to V_{CCA}.
A2	3	3	3	A2	B3	I/O	Input/output 2. Referenced to V_{CCA}.
A3	4	4	4	A3	C3	I/O	Input/output 3. Referenced to V_{CCA}.
A4	5	5	5	A4	D3	I/O	Input/output 4. Referenced to V_{CCA}.
B1	13	13	10	C1	A1	I/O	Input/output 1. Referenced to V_{CCB}.
B2	12	12	9	C2	B1	I/O	Input/output 2. Referenced to V_{CCB}.
B3	11	11	8	C3	C1	I/O	Input/output 3. Referenced to V_{CCB}.
B4	10	10	7	C4	D1	I/O	Input/output 4. Referenced to V_{CCB}.
GND	7	7	6	B4	D2	—	Ground
NC	6, 9	6,9	—	—	—	—	No connection. Not internally connected.
OE	8	8	12	B3	C2	I	Tri-state output-mode enable. Pull OE low to place all outputs in tri-state mode. Referenced to V_{CCA}.
V_{CCA}	1	1	1	B2	B2	—	A-port supply voltage 1.2 V ≤ V_{CCA} ≤ 3.6 V and V_{CCA} ≤ V_{CCB}.
V_{CCB}	14	14	11	B1	A2	—	B-port supply voltage 1.65 V ≤ V_{CCB} ≤ 5.5 V.
Thermal pad	—		—	—	—	—	For the RGY package, the exposed center thermal pad must either be connected to Ground or left electrically open.

表 5-2. Pin Assignments: NMN, GXU and ZXU Package

	A	B	C
4	A4	GND	B4
3	A3	OE	B3
2	A2	V_{CCA}	B2
1	A1	V_{CCB}	B1

表 5-3. Pin Assignments: YZT Package

	3	2	1
D	A4	GND	B4
C	A3	OE	B3
B	A2	V_{CCA}	B2
A	A1	V_{CCB}	B1

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

(1)		MIN	MAX	UNIT
Supply voltage, V_{CCA}		–0.5	4.6	V
Supply voltage, V_{CCB}		–0.5	6.5	
Input voltage, V_I	A port	–0.5	4.6	V
	B port	–0.5	6.5	
Voltage applied to any output in the high-impedance or power-off state, V_O	A port	–0.5	4.6	V
	B port	-0.5	6.5	
Voltage applied to any output in the high or low state, V_O (2)	A port	–0.5	V_{CCA} + 0.5	V
	B port	–0.5	V_{CCB} + 0.5	
Input clamp current, I_{IK}	V_I < 0		–50	mA
Output clamp current, I_{OK}	V_O < 0		–50	mA
Continuous output current, I_O		–50	50	mA
Continuous current through V_{CCA}, V_{CCB}, or GND		–100	100	mA
Junction temperature range, T_J			150	°C
Storage temperature range, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *セクション 6.3* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The value of V_{CCA} and V_{CCB} are provided in the recommended operating conditions table.

6.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	A port	±2.5	kV
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	B port	±15	
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	A port	±1.5	
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	B port	±1.5	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1) (2)

					MIN	MAX	UNIT
V_{CCA}	Supply voltage				1.2	3.6	V
V_{CCB}	Supply voltage				1.65	5.5	V
V_{IH}	High-level input voltage	Data inputs	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V		V_{CCI} × 0.65(3)	V_{CCI}	V
		OE	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V		V_{CCA} × 0.65	5.5	V
V_{IL}	Low-level input voltage	Data inputs	V_{CCA} = 1.2 V to 5.5 V V_{CCB} = 1.65 V to 5.5 V		0	V_{CCI} × 0.35(3)	V
		OE	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V		0	V_{CCA} × 0.35	V
V_O	Voltage applied to any output in the high-impedance or power-off state	A-port	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V		0	3.6	V
		B-port	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V		0	5.5	V
Δt/Δv	Input transition rise or fall rate	A-port inputs	V_{CCA} = 1.2 V to 3.6 V V_{CCB} = 1.65 V to 5.5 V			40	ns/V
		B-port inputs	V_{CCA} = 1.2 V to 3.6 V	V_{CCB} = 1.65 V to 3.6 V		40	ns/V
				V_{CCB} = 4.5 V to 5.5 V		30	ns/V
T_A	Operating free-air temperature				–40	85	°C

(1) The A and B sides of an unused data I/O pair must be held in the same state, that is, both at V_{CCI} or both at GND.
(2) V_{CCA} must be less than or equal to V_{CCB} and must not exceed 3.6 V.
(3) V_{CCI} is the supply voltage associated with the input port.

6.4 Thermal Information

THERMAL METRIC(1)		TXB0104							UNIT
		D	GXU/ZXU	PW	RGY	RUT	YZT	NMN	
		14 PINS	12 PINS	14 PINS	14 PINS	12 PINS	12 PINS	12 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	90.7	127.1	121.0	52.8	119.8	89.2	134.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	50.5	92.8	50.0	67.7	42.6	0.9	90.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	45.4	62.2	62.8	28.9	52.5	14.4	88.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter	14.7	2.3	6.4	2.6	0.7	3.0	4.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	45.1	62.2	62.2	29.0	52.3	14.4	89.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	—	—	—	—	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER[1] [2]		TEST CONDITIONS	V_{CCA}	V_{CCB}	T_A = 25°C			–40°C to 85°C		UNIT
					MIN	TYP	MAX	MIN	MAX	
V_{OHA}	Port A output high voltage	I_{OH} = –20 µA	1.2 V			1.1				V
			1.4 V to 3.6 V					V_{CCA} – 0.4		
V_{OLA}	Port A output low voltage	I_{OL} = 20 µA	1.2 V			0.3				V
			1.4 V to 3.6 V						0.4	
V_{OHB}	Port B output high voltage	I_{OH} = –20 µA		1.65 V to 5.5 V				V_{CCB} – 0.4		V
V_{OLB}	Port B output low voltage	I_{OL} = 20 µA		1.65 V to 5.5 V					0.4	V
I_I	Inflection-point current	OE: $V_I = V_{CCI}$ or GND	1.2 V to 3.6 V	1.65 V to 5.5 V	–1		1	–2	2	µA
I_{off}	Off-state current	A port: V_I or V_O = 0 to 3.6 V	0 V	0 V to 5.5 V	–1		1	–2	2	µA
		B port: V_I or V_O = 0 to 5.5 V	0 V to 3.6 V	0 V	–1		1	–2	2	
I_{OZ}	High-impedance-state output current	A or B port: OE = GND	1.2 V to 3.6 V	1.65 V to 5.5 V	–1		1	–2	2	µA
I_{CCA}	V_{CCA} supply current	$V_I = V_{CCI}$ or GND, I_O = 0	1.2 V	1.65 V to 5.5 V		0.06				µA
			1.4 V to 3.6 V	1.65 V to 5.5 V					5	
			3.6 V	0 V					2	
			0 V	5.5 V					–2	
I_{CCB}	V_{CCB} supply current	$V_I = V_{CCI}$ or GND, I_O = 0	1.2 V	1.65 V to 5.5 V		3.4				µA
			1.4 V to 3.6 V	1.65 V to 5.5 V					5	
			3.6 V	0 V					–2	
			0 V	5.5 V					2	
I_{CCA} + I_{CCB}	Combined supply current	$V_I = V_{CCI}$ or GND, I_O = 0	1.2 V	1.65 V to 5.5 V		3.5				µA
			1.4 V to 3.6 V	1.65 V to 5.5 V					10	
I_{CCZA}	High-impedance state, V_{CCA} supply current	$V_I = V_{CCI}$ or GND, I_O = 0, OE = GND	1.2 V	1.65 V to 5.5 V		0.05				µA
			1.4 V to 3.6 V	1.65 V to 5.5 V					5	
I_{CCZB}	High-impedance state, V_{CCB} supply current	$V_I = V_{CCI}$ or GND, I_O = 0, OE = GND	1.2 V	1.65 V to 5.5 V		3.3				µA
			1.4 V to 3.6 V	1.65 V to 5.5 V					5	
C_i	Input capacitance	OE	1.2 V to 3.6 V	1.65 V to 5.5 V		3			4	pF
C_{io}	Input-to-output internal capacitance	A port	1.2 V to 3.6 V	1.65 V to 5.5 V		5			6	pF
		B port	1.2 V to 3.6 V	1.65 V to 5.5 V		11			14	

(1) V_{CCI} is the supply voltage associated with the input port.
(2) V_{CCO} is the supply voltage associated with the output port.

6.6 Timing Requirements: V_{CCA} = 1.2 V

T_A = 25°C, V_{CCA} = 1.2 V

			V_{CCB} = 1.8 V			V_{CCB} = 2.5 V			V_{CCB} = 3.3 V			V_{CCB} = 5 V			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
	Data rate			20			20			20			20		Mbps
t_w	Pulse duration	Data inputs		50			50			50			50		ns

6.7 Timing Requirements: V_{CCA} = 1.5 V ± 0.1 V

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

			V_{CCB} = 1.8 V ± 0.15 V		V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Data rate			40		40		40		40	Mbps
t_w	Pulse duration	Data inputs	25		25		25		25		ns

6.8 Timing Requirements: V_{CCA} = 1.8 V ± 0.15 V

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted)

			V_{CCB} = 1.8 V ± 0.15 V		V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Data rate			60		60		60		60	Mbps
t_w	Pulse duration	Data inputs	17		17		17		17		ns

6.9 Timing Requirements: V_{CCA} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (unless otherwise noted)

			V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
	Data rate			100		100		100	Mbps
t_w	Pulse duration	Data inputs	10		10		10		ns

6.10 Timing Requirements: V_{CCA} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted)

			V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	
	Data rate			100		100	Mbps
t_w	Pulse duration	Data inputs	10		10		ns

6.11 Switching Characteristics: V_{CCA} = 1.2 V

T_A = 25°C, V_{CCA} = 1.2 V

PARAMETER		TEST CONDITIONS	V_{CCB} = 1.8 V			V_{CCB} = 2.5 V			V_{CCB} = 3.3 V			V_{CCB} = 5 V			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	Propagation delay time	A-to-B		6.9			5.7			5.3			5.5		ns
		B-to-A		7.4			6.4			6			5.8		
t_{en}	Enable time	OE-to-A		1			1			1			1		µs
		OE-to-B		1			1			1			1		
t_{dis}	Disable time	OE-to-A		18			15			14			14		ns
		OE-to-B		20			17			16			16		
t_{rA}, t_{fA}	Input rise time, input fall time	A-port rise and fall times		4.2			4.2			4.2			4.2		ns
t_{rB}, t_{fB}	Input rise time, input fall time	B-port rise and fall times		2.1			1.5			1.2			1.1		ns
$t_{SK(O)}$	Skew (time), output	Channel-to-channel skew		0.4			0.5			0.5			1.4		ns
	Maximum data rate		20			20			20			20			Mbps

6.12 Switching Characteristics: V_{CCA} = 1.5 V ± 0.1 V

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CCB} = 1.8 V ± 0.15 V		V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	Propagation delay time	A-to-B	1.4	12.9	1.2	10.1	1.1	10	0.8	9.9	ns
		B-to-A	0.9	14.2	0.7	12	0.4	11.7	0.3	13.7	
t_{en}	Enable time	OE-to-A		1		1		1		1	µs
		OE-to-B		1		1		1		1	
t_{dis}	Disable time	OE-to-A	5.9	31	5.7	25.9	5.6	23	5.7	22.4	ns
		OE-to-B	5.4	30.3	4.9	22.8	4.8	20	4.9	19.5	
t_{rA}, t_{fA}	Input rise time, input fall time	A-port rise and fall times	1.4	5.1	1.4	5.1	1.4	5.1	1.4	5.1	ns
t_{rB}, t_{fB}	Input rise time, input fall time	B-port rise and fall times	0.9	4.5	0.6	3.2	0.5	2.8	0.4	2.7	ns
$t_{SK(O)}$	Skew (time), output	Channel-to-channel skew		0.5		0.5		0.5		0.5	ns
	Maximum data rate		40		40		40		40		Mbps

6.13 Switching Characteristics: V_{CCA} = 1.8 V ± 0.15 V

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CCB} = 1.8 V ± 0.15 V		V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	Propagation delay time	A-to-B	1.6	11	1.4	7.7	1.3	6.8	1.2	6.5	ns
		B-to-A	1.5	12	1.3	8.4	1	7.6	0.9	7.1	
t_{en}	Enable time	OE-to-A		1		1		1		1	µs
		OE-to-B		1		1		1		1	
t_{dis}	Disable time	OE-to-A	5.9	31	5.1	21.3	5	19.3	5	17.4	ns
		OE-to-B	5.4	30.3	4.4	20.8	4.2	17.9	4.3	16.3	
t_{rA}, t_{fA}	Input rise time, input fall time	A-port rise and fall times	1	4.2	1.1	4.1	1.1	4.1	1.1	4.1	ns
t_{rB}, t_{fB}	Input rise time, input fall time	B-port rise and fall times	0.9	3.8	0.6	3.2	0.5	2.8	0.4	2.7	ns
$t_{SK(O)}$	Skew (time), output	Channel-to-channel skew		0.5		0.5		0.5		0.5	ns
	Maximum data rate		60		60		60		60		Mbps

6.14 Switching Characteristics: V_{CCA} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CCB} = 2.5 V ± 0.2 V		V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	Propagation delay time	A-to-B	1.1	6.3	1	5.2	0.9	4.7	ns
		B-to-A	1.2	6.6	1.1	5.1	0.9	4.4	
t_{en}	Enable time	OE-to-A		1		1		1	µs
		OE-to-B		1		1		1	
t_{dis}	Disable time	OE-to-A	5.1	21.3	4.6	15.2	4.6	13.2	ns
		OE-to-B	4.4	20.8	3.8	16	3.9	13.9	
t_{rA}, t_{fA}	Input rise time, input fall time	A-port rise and fall times	0.8	3	0.8	3	0.8	3	ns
t_{rB}, t_{fB}	Input rise time, input fall time	B-port rise and fall times	0.7	2.6	0.5	2.8	0.4	2.7	ns
$t_{SK(O)}$	Skew (time), output	Channel-to-channel skew		0.5		0.5		0.5	ns
	Maximum data rate		100		100		100		Mbps

6.15 Switching Characteristics: V_{CCA} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CCB} = 3.3 V ± 0.3 V		V_{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	Propagation delay time	A-to-B	0.9	4.7	0.8	4	ns
		B-to-A	1	4.9	0.9	3.8	
t_{en}	Enable time	OE-to-A		1		1	µs
		OE-to-B		1		1	
t_{dis}	Disable time	OE-to-A	4.6	15.2	4.3	12.1	ns
		OE-to-B	3.8	16	3.4	13.2	
t_{rA}, t_{fA}	Input rise time, input fall time	A-port rise and fall times	0.7	2.5	0.7	2.5	ns
t_{rB}, t_{fB}	Input rise time, input fall time	B-port rise and fall times	0.5	2.1	0.4	2.7	ns
$t_{SK(O)}$	Skew (time), output	Channel-to-channel skew		0.5		0.5	ns
	Maximum data rate		100		100		Mbps

6.16 Operating Characteristics: V_{CCA} = 1.2 V to 1.5 V, V_{CCB} = 1.5 V to 1.8 V

T_A = 25°C

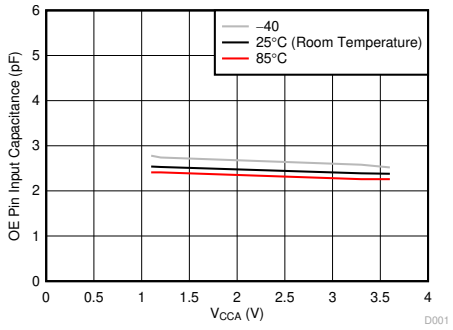
PARAMETER		TEST CONDITIONS		V_{CCA} = 1.2 V, V_{CCB} =1.5 V			V_{CCA} = 1.2 V, V_{CCB} = 1.8 V			V_{CCA} = 1.5 V, V_{CCB} = 1.8 V			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
C_{pdA}	Power dissipation capacitance	C_L = 0 f = 10 MHz $t_r = t_f$ = 1 ns OE = V_{CCA} (outputs enabled)	A-port input, B-port output		7.8			10			9		pF
			B-port input, A-port output		12			11			11		
C_{pdB}	Power dissipation capacitance		A-port input, B-port output		38.1			28			28		
			B-port input, A-port output		25.4			19			18		
C_{pdA}	Power dissipation capacitance	C_L = 0 f = 10 MHz $t_r = t_f$ = 1 ns OE = GND (outputs disabled)	A-port input, B-port output		0.01			0.01			0.01		pF
			B-port input, A-port output		0.01			0.01			0.01		
C_{pdB}	Power dissipation capacitance		A-port input, B-port output		0.01			0.01			0.01		
			B-port input, A-port output		0.01			0.01			0.01		

6.17 Operating Characteristics: V_{CCA} = 1.8 V to 3.3 V, V_{CCB} = 1.8 V to 5 V

T_A = 25°C

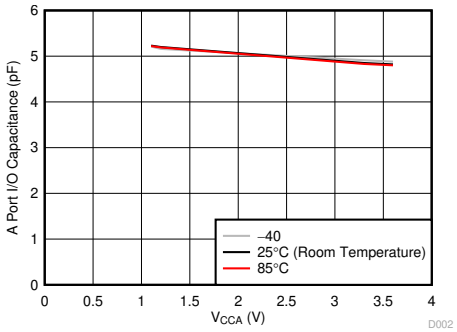
PARAMETER		TEST CONDITIONS		V_{CCA} = 1.8 V, V_{CCB} =1.8 V			V_{CCA} = 2.5 V, V_{CCB} = 2.5 V			V_{CCA} = 2.5 V, V_{CCB} = 5 V			V_{CCA} = 3.3 V, V_{CCB} = 3.3 V to 5 V			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
C_{pdA}	Power dissipation capacitance	C_L = 0 f = 10 MHz $t_r = t_f$ = 1 ns OE = V_{CCA} (outputs enabled)	A-port input, B-port output		8			8			8			9		pF
			B-port input, A-port output		11			11			11			11		
C_{pdB}	Power dissipation capacitance		A-port input, B-port output		28			29			29			29		
			B-port input, A-port output		18			19			21			22		
C_{pdA}	Power dissipation capacitance	C_L = 0 f = 10 MHz $t_r = t_f$ = 1 ns OE = GND (outputs disabled)	A-port input, B-port output		0.01			0.01			0.01			0.01		pF
			B-port input, A-port output		0.01			0.01			0.01			0.01		
C_{pdB}	Power dissipation capacitance		A-port input, B-port output		0.01			0.01			0.01			0.03		
			B-port input, A-port output		0.01			0.01			0.01			0.04		

6.18 Typical Characteristics



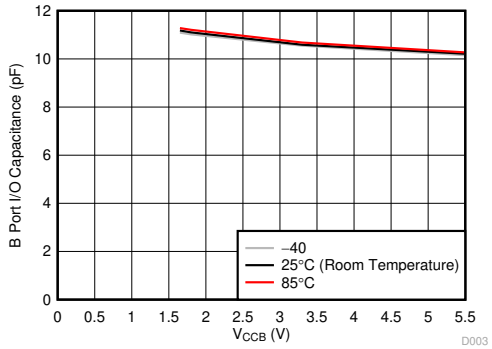
V_{CCB}= 3.3 V

図 6-1. Input Capacitance for OE Pin (C_I) vs Power Supply (V_{CCA})



V_{CCB}= 3.3 V

図 6-2. Capacitance for A port I/O Pins (C_{IO}) vs Power Supply (V_{CCA})



V_{CCA}= 1.8 V

図 6-3. Capacitance for B Port I/O Pins (C_{IO}) vs Power Supply (V_{CCB})

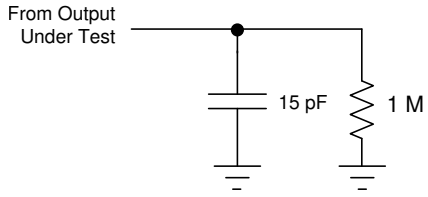
7 Parameter Measurement Information

Unless otherwise noted, all input pulses are supplied by generators that have the following characteristics:

- PRR 10 MHz
- Z_O = 50 W
- dv/dt ≥ 1 V/ns

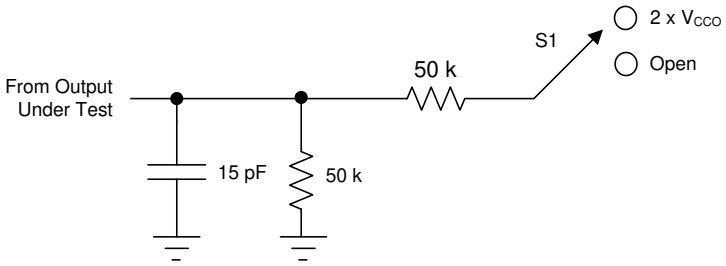
Note

All parameters and waveforms are not applicable to all devices.



A. The outputs are measured one at a time, with one transition per measurement.

図 7-1. Load Circuit For Maximum Data Rate: Pulse Duration, Propagation Delay Output Rise, And Fall Time Measurement

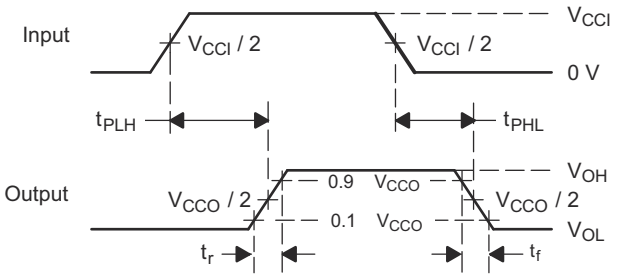


A. The outputs are measured one at a time, with one transition per measurement.

図 7-2. Load Circuit For Enable and Disable Time Measurement

表 7-1. Switch Position For Enable and Disable Time Measurement (See 図 7-2)

TEST	S1
t_{PZL}, t_{PLZ}	2 × V_{CCO}
t_{PHZ}, t_{PZH}	Open



A. V_{CCI} is the V_{CC} associated with the input port.
B. V_{CCO} is the$_{VCC}$ associated with the output port.
C. t_{PLH} and t_{PHL} are the same as t_{pd}.
D. The outputs are measured one at a time, with one transition per measurement.

図 7-3. Voltage Waveforms Propagation Delay Times

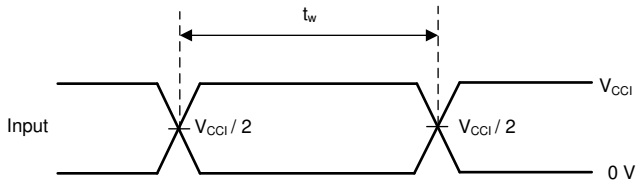


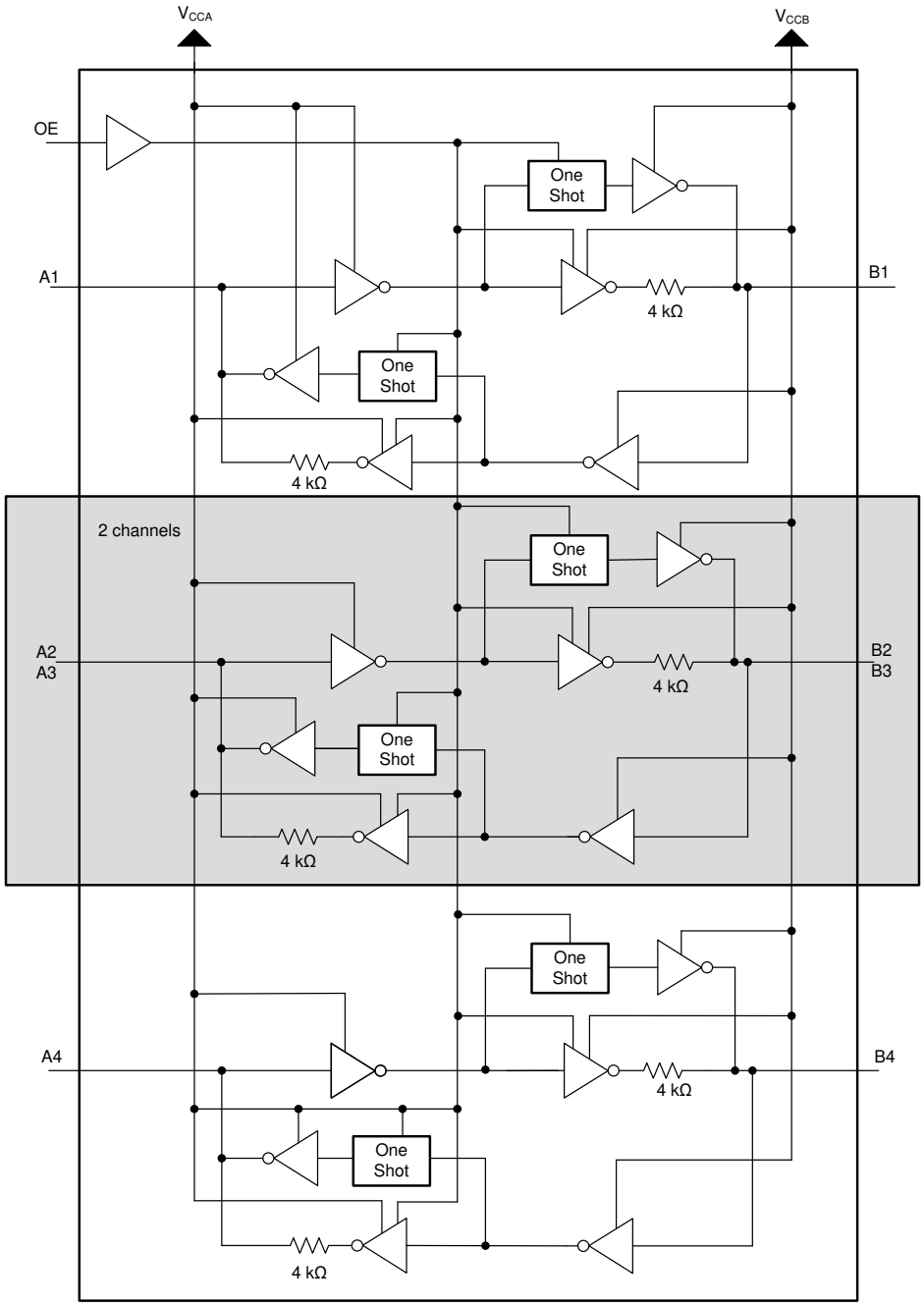
図 7-4. Voltage Waveforms Pulse Duration

8 Detailed Description

8.1 Overview

The TXB0104 device is a 4-bit, directionless voltage-level translator specifically designed for translating logic voltage levels. The A port is able to accept I/O voltages ranging from 1.2 V to 3.6 V, while the B port can accept I/O voltages from 1.65 V to 5.5 V. The device is a buffered architecture with edge-rate accelerators (one-shots) to improve the overall data rate. This device can only translate push-pull CMOS logic outputs. If for open-drain signal translation, please refer to TI's TXS010X products.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Architecture

The TXB0104 device architecture (see 図 8-1) does not require a direction-control signal to control the direction of data flow from A to B or from B to A. In a DC state, the output drivers of the device maintain a high or low, but are designed to be weak, so the output drivers can be overdriven by an external driver when data on the bus flows the opposite direction.

The output one-shots detect rising or falling edges on the A or B ports. During a rising edge, the one-shot turns on the PMOS transistors (T1, T3) for a short duration, which speeds up the low-to-high transition. Similarly, during a falling edge, the one-shot turns on the NMOS transistors (T2, T4) for a short duration, which speeds up the high-to-low transition. The typical output impedance during output transition is 70 Ω at V_{CCO} = 1.2 V to 1.8 V, 50 Ω at V_{CCO} = 1.8 V to 3.3 V, and 40 Ω at V_{CCO} = 3.3 V to 5 V.

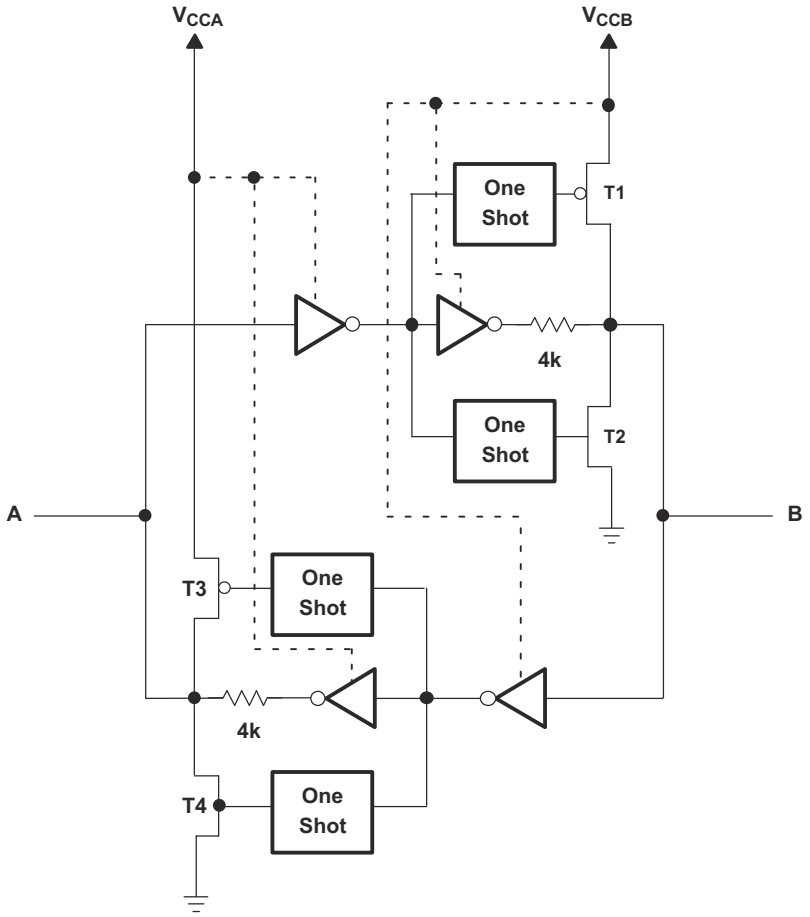
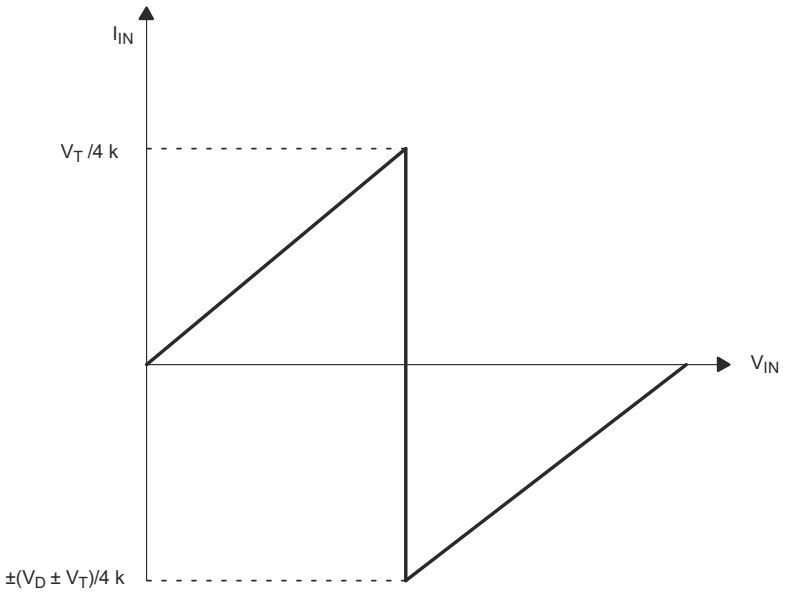


図 8-1. Architecture of TXB0104 Device I/O Cell

8.3.2 Input Driver Requirements

Typical I_{IN} vs V_{IN} characteristics of the device are shown in 図 8-2. For proper operation, the device driving the data I/Os of the TXB0104 device must have drive strength of at least ±2 mA.



A. V_T is the input threshold of the TXB0104 device, (typically V_{CC} / 2).
B. V_D is the supply voltage of the external driver.

図 8-2. Typical I_{IN} vs V_{IN} Curve

8.3.3 Output Load Considerations

TI recommends careful PCB layout practices with short PCB trace lengths to avoid excessive capacitive loading and to ensure that proper O.S. triggering takes place. PCB signal trace-lengths must be kept short enough such that the round trip delay of any reflection is less than the one-shot duration. This improves signal integrity by ensuring that any reflection sees a low impedance at the driver. The O.S. circuits have been designed to stay on for approximately 10 ns. The maximum capacitance of the lumped load that can be driven also depends directly on the one-shot duration. With very heavy capacitive loads, the one-shot can time-out before the signal is driven fully to the positive rail. The O.S. duration has been set to best optimize trade-offs between dynamic ICC, load driving capability, and maximum bit-rate considerations. Both PCB trace length and connectors add to the capacitance that the device output sees, so it is recommended that this lumped-load capacitance be considered to avoid O.S. retriggering, bus contention, output signal oscillations, or other adverse system-level affects.

8.3.4 Enable and Disable

The TXB0104 device has an OE input that is used to disable the device by setting OE = low, which places all I/Os in the high-impedance (Hi-Z) state. The disable time (t_{dis}) indicates the delay between when OE goes low and when the outputs acutally get disabled (Hi-Z). The enable time (t_{en}) indicates the amount of time the user must allow for the one-shot circuitry to become operational after OE is taken high.

8.3.5 Pullup or Pulldown Resistors on I/O Lines

The device is designed to drive capacitive loads of up to 70 pF. The output drivers of the TXB0104 device have low dc drive strength. If pullup or pulldown resistors are connected externally to the data I/Os, their values must be kept higher than 50 kΩ to ensure that they do not contend with the output drivers of the TXB0104 device.

For the same reason, the TXB0104 device must not be used in applications such as I^2C or 1-Wire where an open-drain driver is connected on the bidirectional data I/O. For these applications, use a device from the TI TXS01xx series of level translators.

8.4 Device Functional Modes

The device has two functional modes, enabled and disabled. To disable the device, set the OE input to low, which places all I/Os in a high impedance state. Setting the OE input to high will enable the device.

9 Application and Implementation

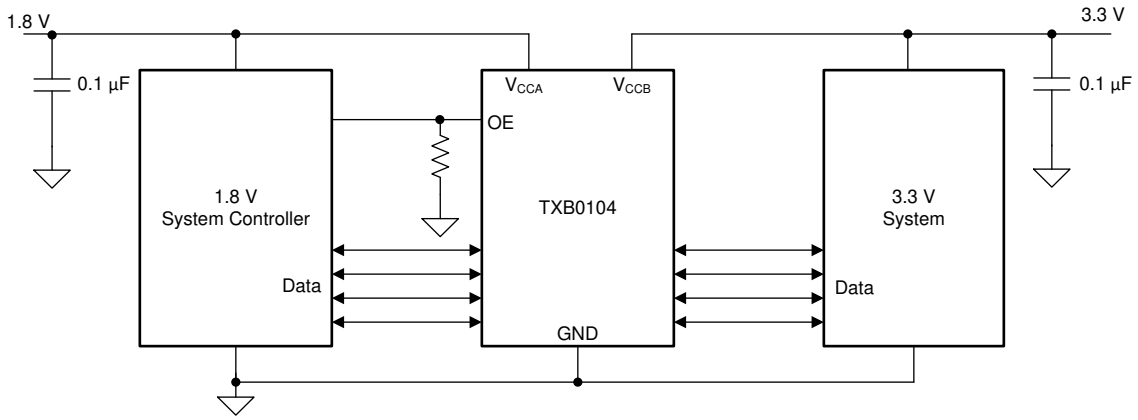
Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

The TXB0104 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. It can only translate push-pull CMOS logic outputs. If for open-drain signal translation, please refer to TI TXS010X products. Any external pulldown or pullup resistors are recommended larger than 50 kΩ.

9.2 Typical Application



9.2.1 Design Requirements

For this design example, use the parameters listed in 表 9-1. And make sure the $V_{CCA} \leq V_{CCB}$.

表 9-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUE
Input voltage range	1.2 V to 3.6 V
Output voltage range	1.65 V to 5.5 V

9.2.2 Detailed Design Procedure

To begin the design process, determine the following:

• Input voltage range

- Use the supply voltage of the device that is driving the TXB0104 device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port.

• Output voltage range

- Use the supply voltage of the device that the device is driving to determine the output voltage range.

- External pullup or pulldown resistors are not recommended. If mandatory, it is recommended that the value must be larger than 50 kΩ.

• An external pulldown or pullup resistor decreases the output V_{OH} and V_{OL}. Use the below equations to draft estimate the V_{OH} and V_{OL} as a result of an external pulldown and pullup resistor.

$V_{OH} = V_{CCx} \times R_{PD} / (R_{PD} + 4.5\ k\Omega)$

$V_{OL} = V_{CCx} \times 4.5\ k\Omega / (R_{PU} + 4.5\ k\Omega)$

Where

• V_{CCx} is the output port supply voltage on either V_{CCA} or V_{CCB}

• R_{PD} is the value of the external pull down resistor

• R_{PU} is the value of the external pull up resistor

• 4.5 kΩ is the counting the variation of the serial resistor 4 kΩ in the I/O line.

9.2.3 Application Curves

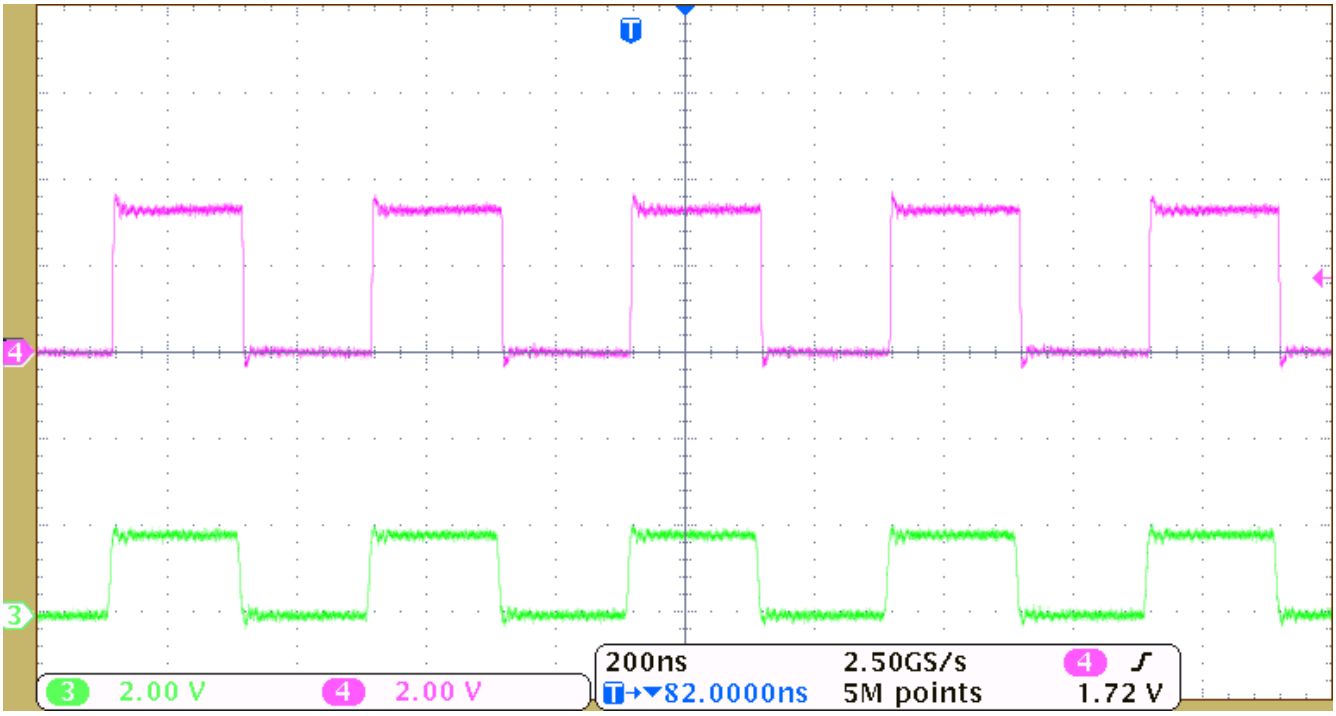


図 9-1. Level-Translation of a 2.5-MHz Signal

10 Power Supply Recommendations

During operation, ensure that $V_{CCA} \leq V_{CCB}$ at all times. During power-up sequencing, $V_{CCA} \geq V_{CCB}$ does not damage the device, so any power supply can be ramped up first. The device has circuitry that disables all output ports when either V_{CC} is switched off ($V_{CCA/B}$ = 0 V). The output-enable (OE) input circuit is designed so that it is supplied by V_{CCA} and when the (OE) input is low, all outputs are placed in the high-impedance state. To ensure the high-impedance state of the outputs during power up or power down, the OE input pin must be tied to GND through a pulldown resistor and must not be enabled until V_{CCA} and V_{CCB} are fully ramped and stable. The minimum value of the pulldown resistor to ground is determined by the current-sourcing capability of the driver.

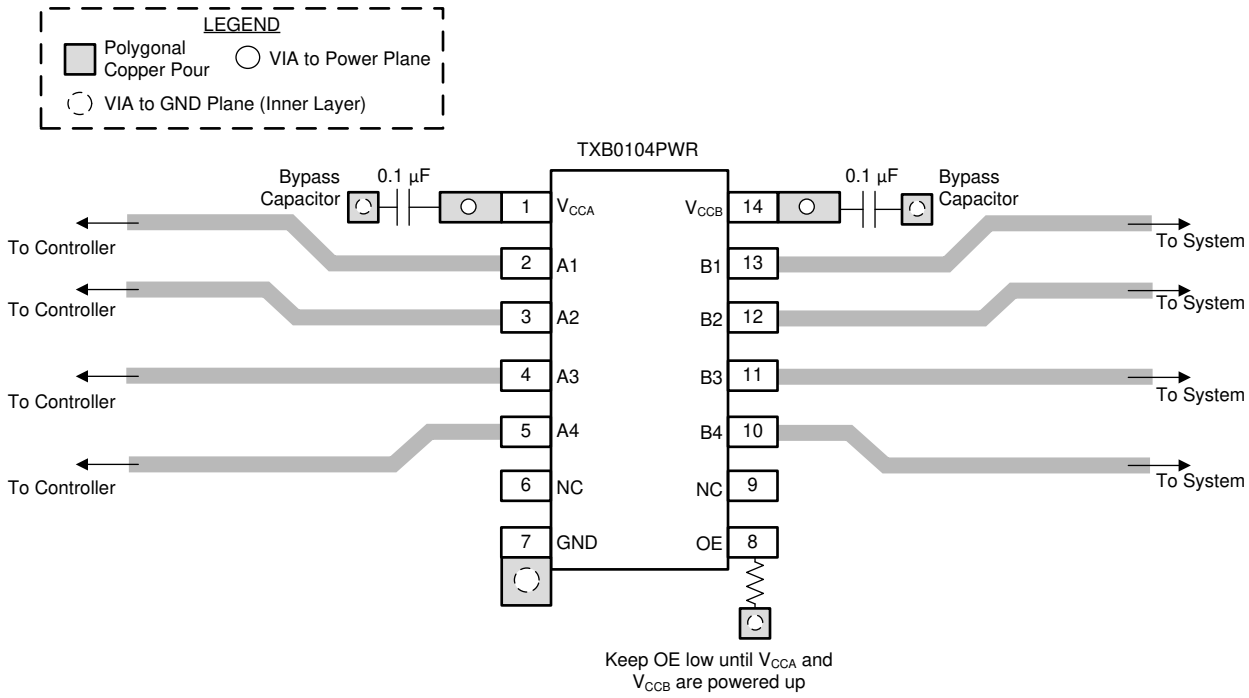
11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- Bypass capacitors must be used on power supplies, and must be placed as close as possible to the V_{CCA}, V_{CCB} pin and GND pin.
- Short trace-lengths must be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one-shot duration, approximately 10 ns, ensuring that any reflection encounters low impedance at the source driver.

11.2 Layout Example



12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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12.3 Trademarks

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TI E2E™ is a trademark of Texas Instruments.
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12.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

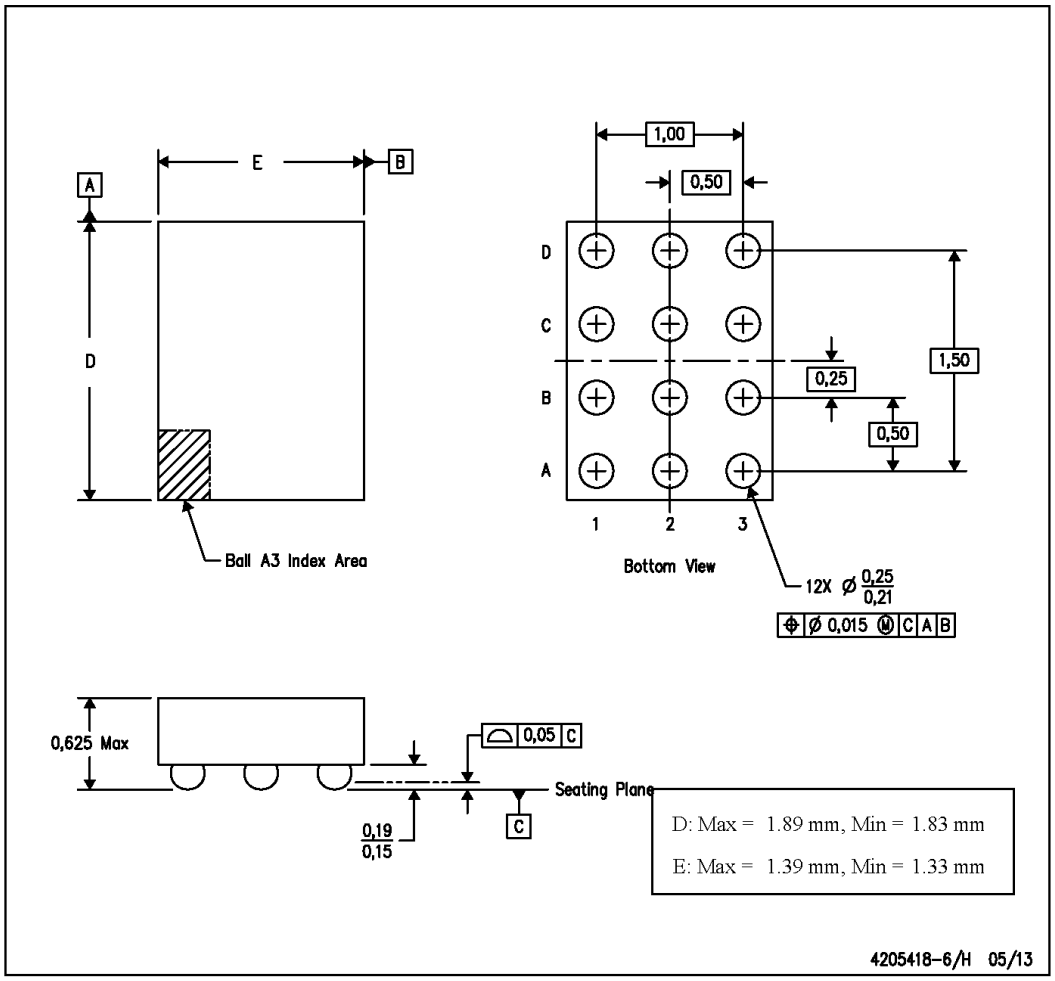
TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

MECHANICAL DATA

YZT (R–XBGA–N12) (CUSTOM) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TXB0104D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXB0104	Samples
TXB0104DG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXB0104	Samples
TXB0104DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXB0104	Samples
TXB0104DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXB0104	Samples
TXB0104NMNR	ACTIVE	NFBGA	NMN	12	2500	RoHS & Green	SNAGCU	Level-2-260C-1 YEAR	-40 to 85	2AQW	Samples
TXB0104PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YE04	Samples
TXB0104PWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YE04	Samples
TXB0104RGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YE04	Samples
TXB0104RGYRG4	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YE04	Samples
TXB0104RUTR	ACTIVE	UQFN	RUT	12	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(2KR, 2KV)	Samples
TXB0104YZTR	ACTIVE	DSBGA	YZT	12	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	2K	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF TXB0104 :

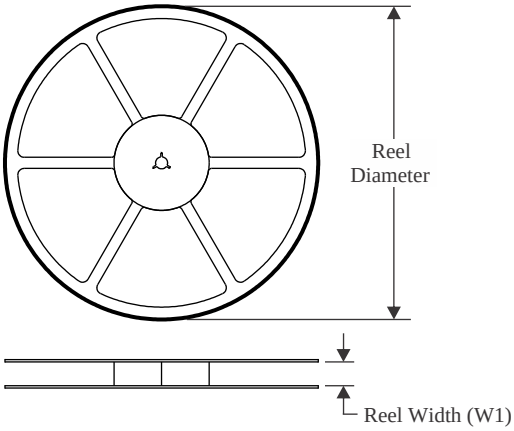
- Automotive : TXB0104-Q1

NOTE: Qualified Version Definitions:

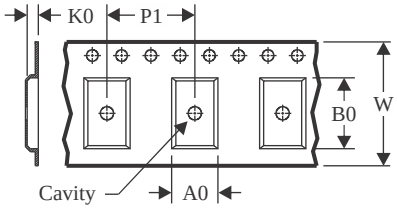
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

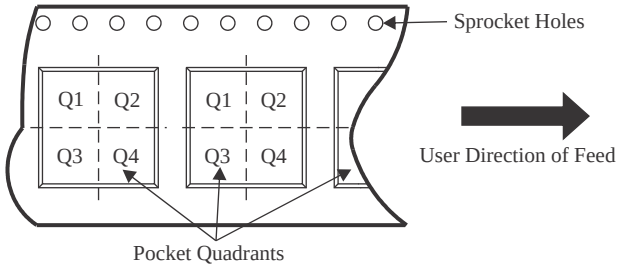


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

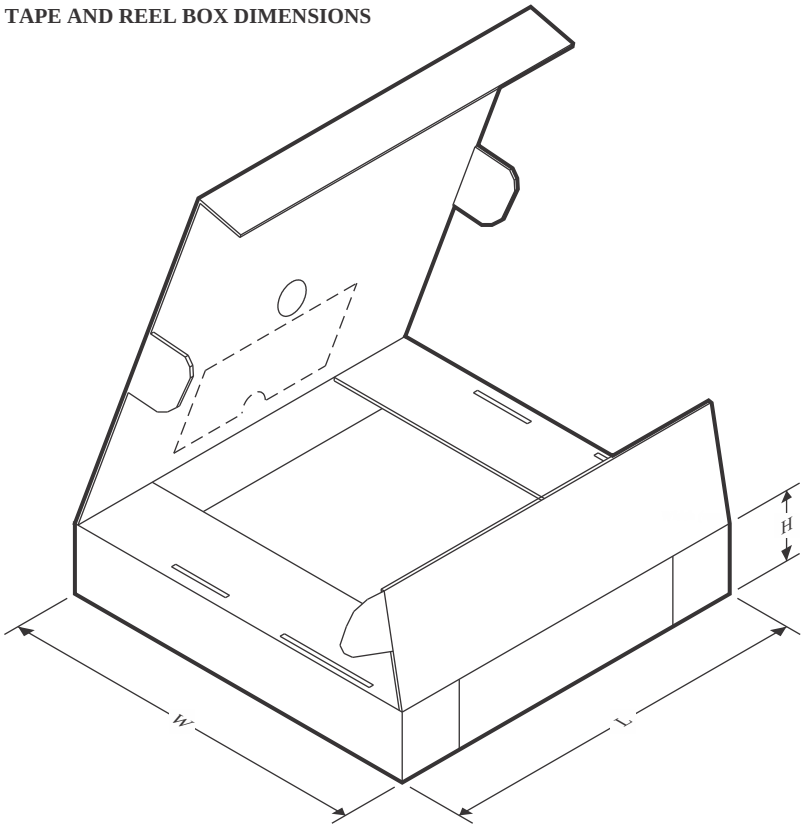
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TXB0104DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TXB0104NMNR	NFBGA	NMN	12	2500	180.0	8.4	2.3	2.8	1.15	4.0	8.0	Q2
TXB0104PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TXB0104RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
TXB0104RUTR	UQFN	RUT	12	3000	180.0	8.4	1.95	2.3	0.75	4.0	8.0	Q1
TXB0104RUTR	UQFN	RUT	12	3000	180.0	9.5	1.9	2.2	0.7	4.0	8.0	Q1
TXB0104YZTR	DSBGA	YZT	12	3000	180.0	8.4	1.49	1.99	0.75	4.0	8.0	Q2

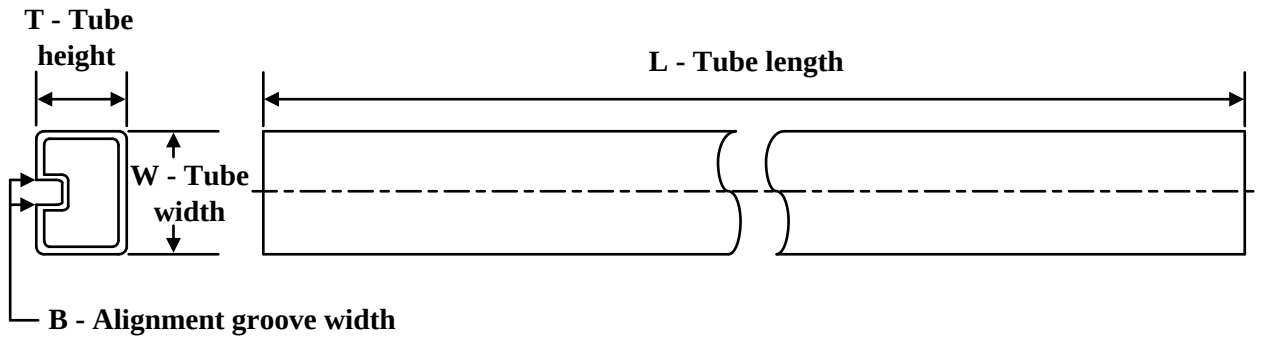
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

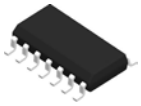
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TXB0104DR	SOIC	D	14	2500	356.0	356.0	35.0
TXB0104NMNR	NFBGA	NMN	12	2500	210.0	185.0	35.0
TXB0104PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
TXB0104RGYR	VQFN	RGY	14	3000	356.0	356.0	35.0
TXB0104RUTR	UQFN	RUT	12	3000	202.0	201.0	28.0
TXB0104RUTR	UQFN	RUT	12	3000	189.0	185.0	36.0
TXB0104YZTR	DSBGA	YZT	12	3000	182.0	182.0	20.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TXB0104D	D	SOIC	14	50	506.6	8	3940	4.32
TXB0104DG4	D	SOIC	14	50	506.6	8	3940	4.32

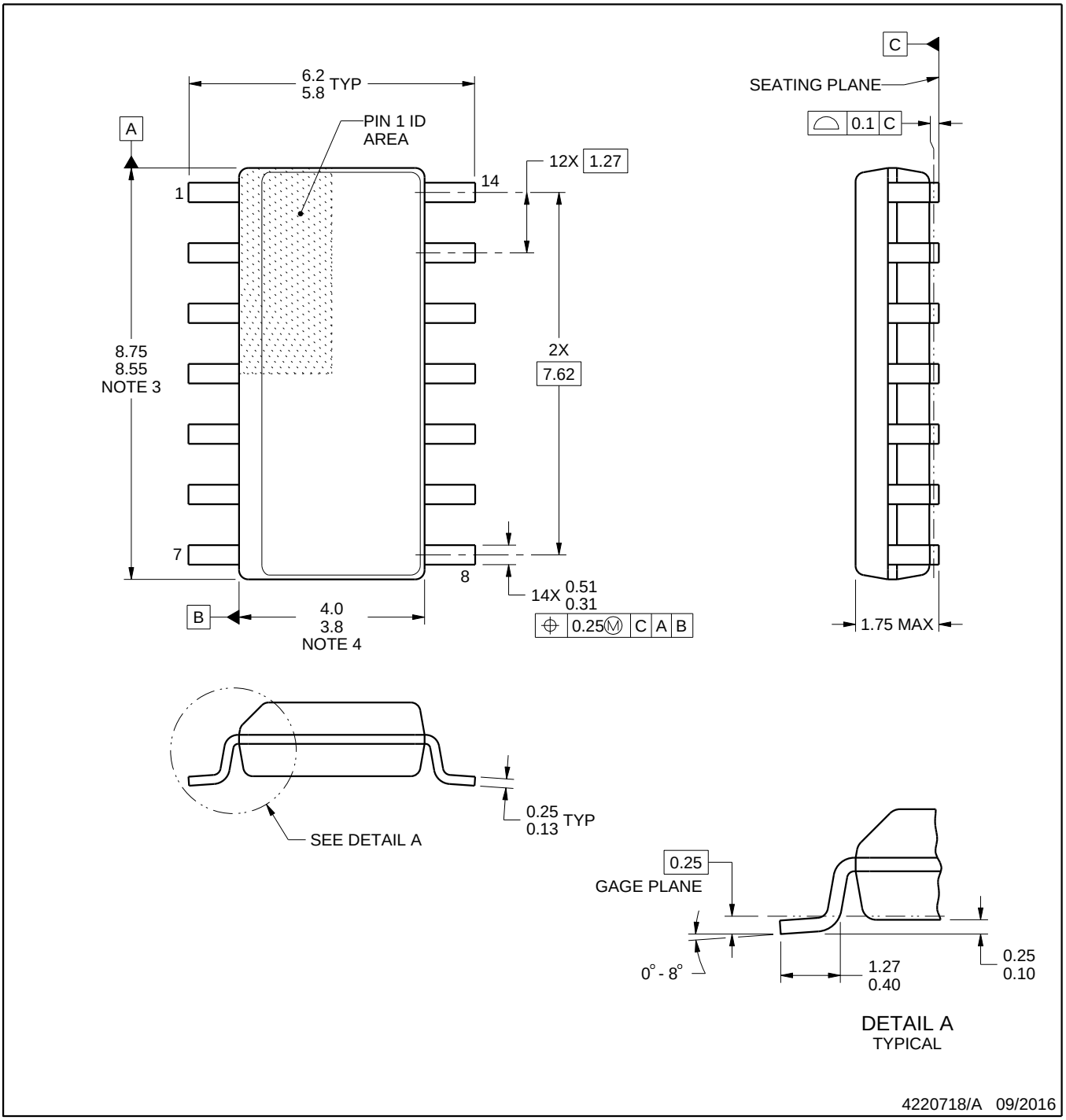


PACKAGE OUTLINE

D0014A

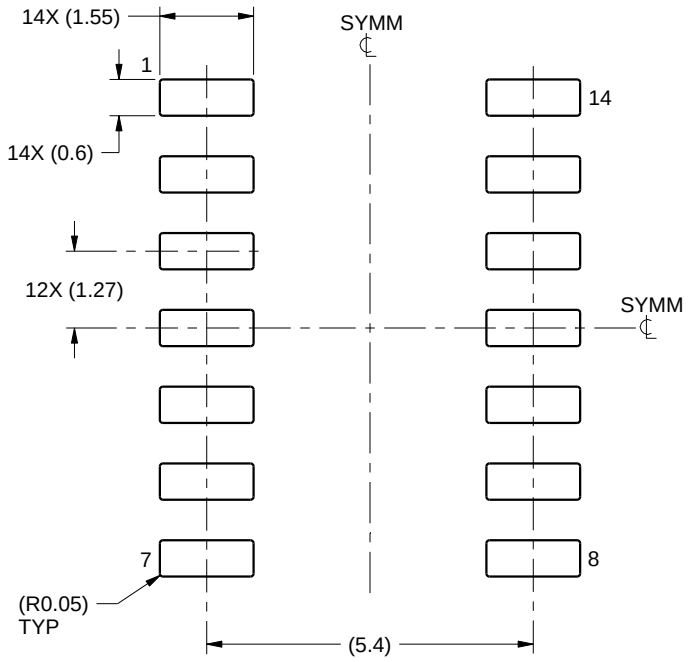
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

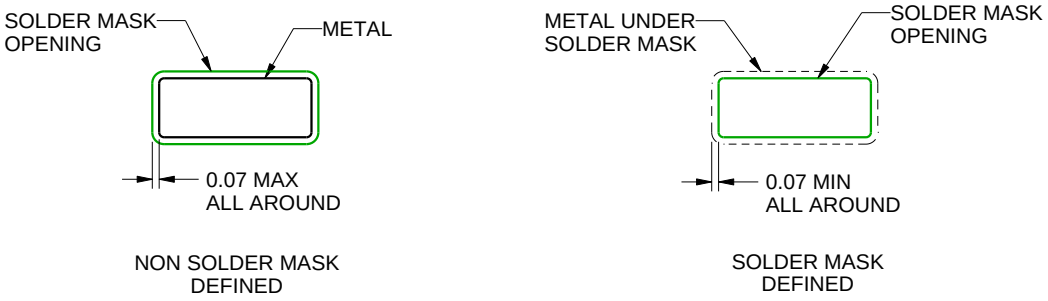


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

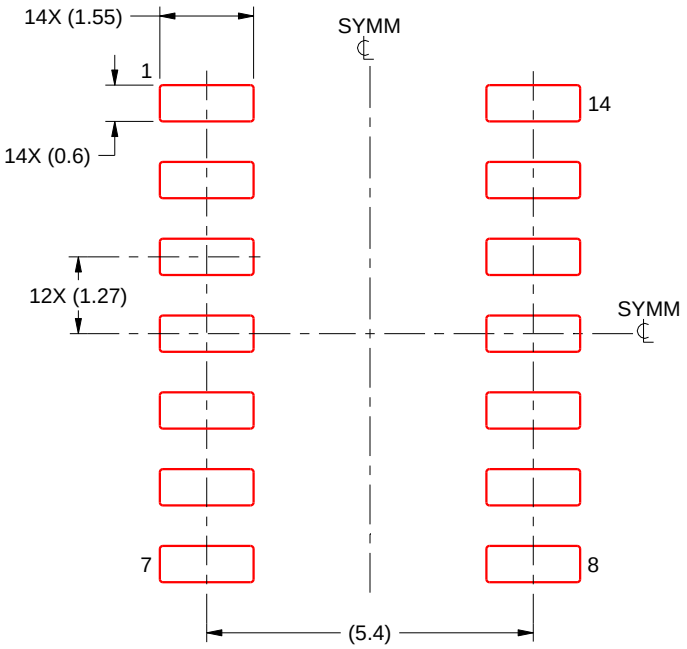
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



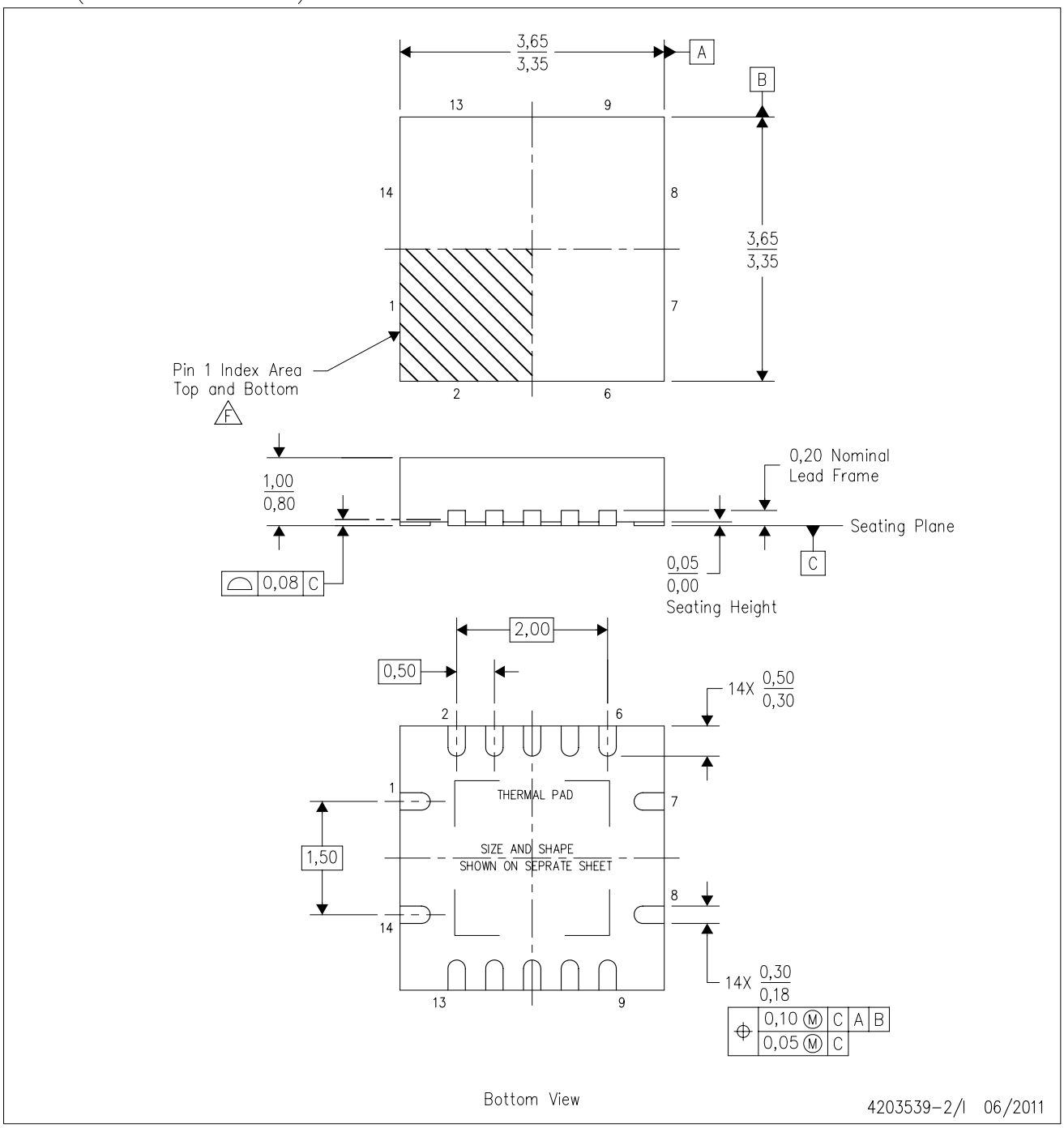
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (S–PVQFN–N14) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No–Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
G. Package complies to JEDEC MO–241 variation BA.

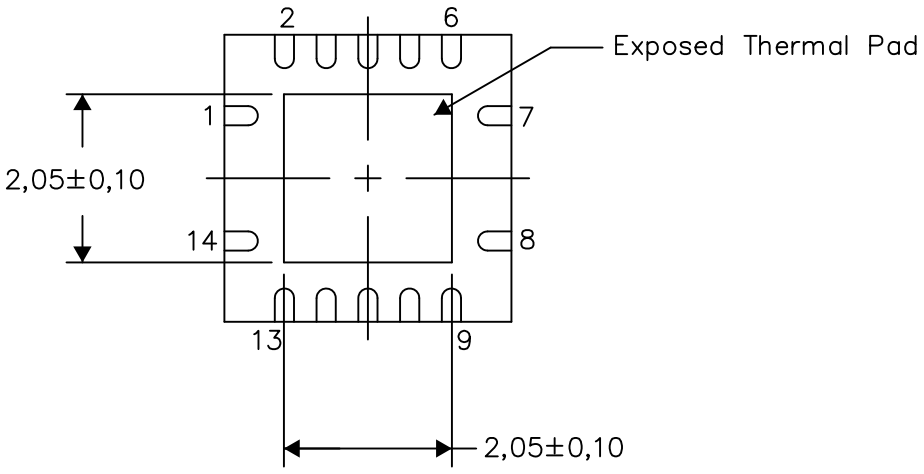
RGY (S–PVQFN–N14) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



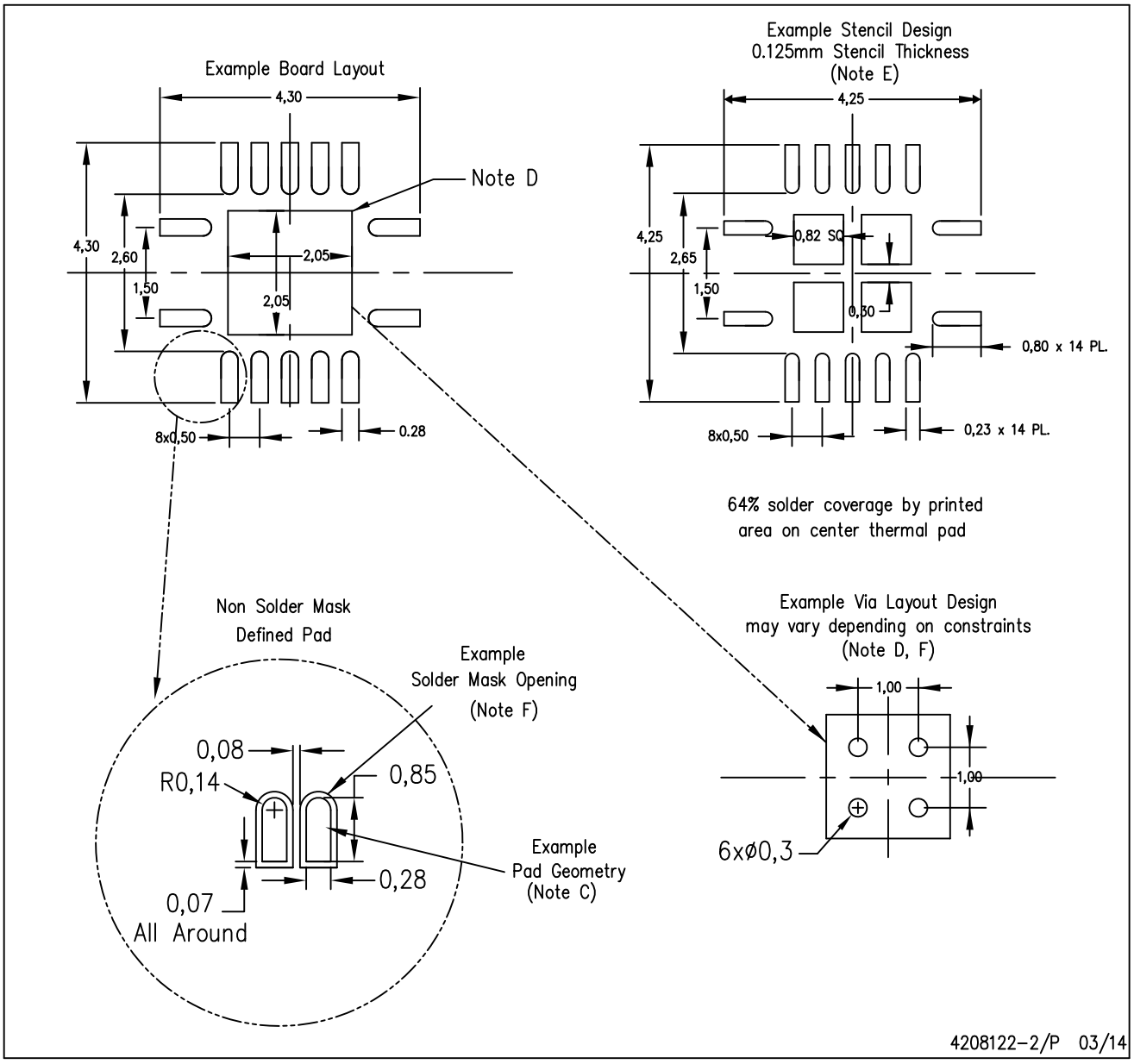
Bottom View

Exposed Thermal Pad Dimensions

4206353–2/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (S–PVQFN–N14) PLASTIC QUAD FLATPACK NO–LEAD



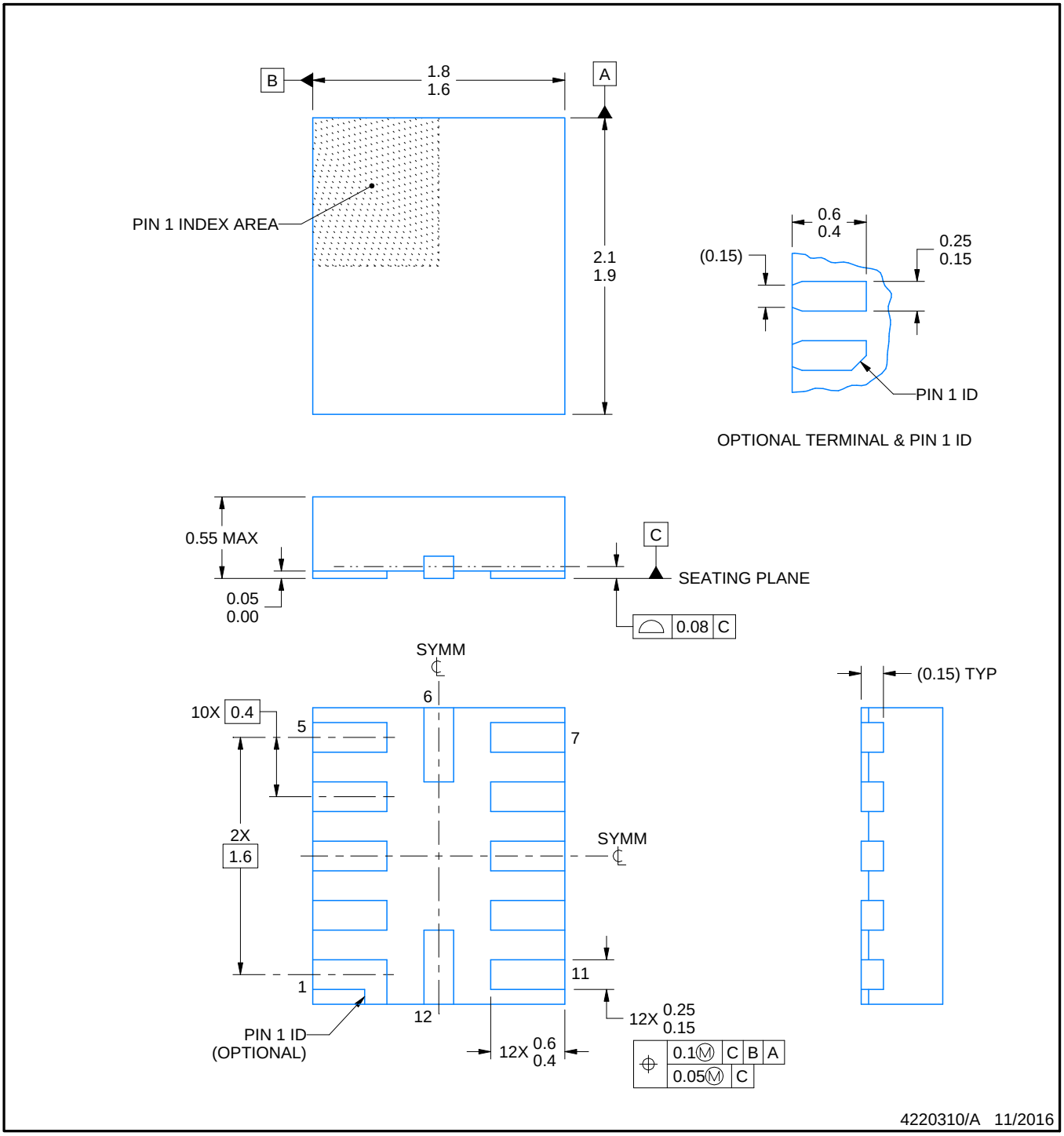
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat–Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

RUT0012A

PACKAGE OUTLINE

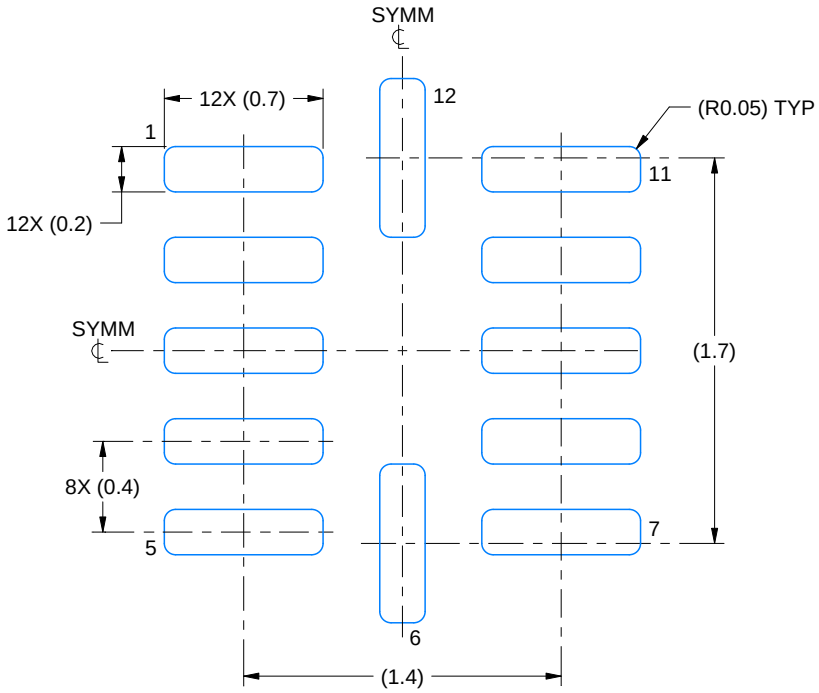
UQFN - 0.55 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

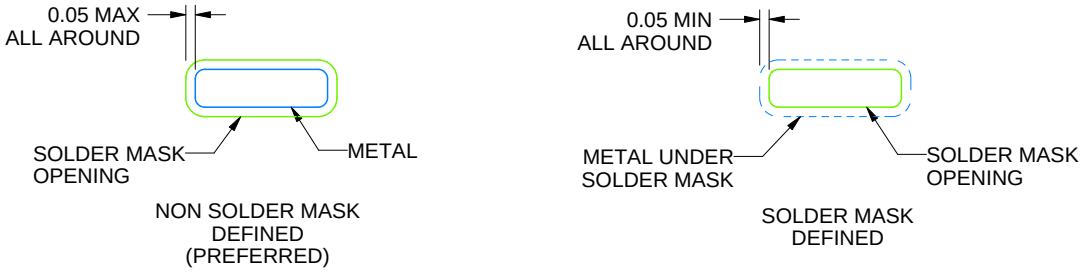


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:30X

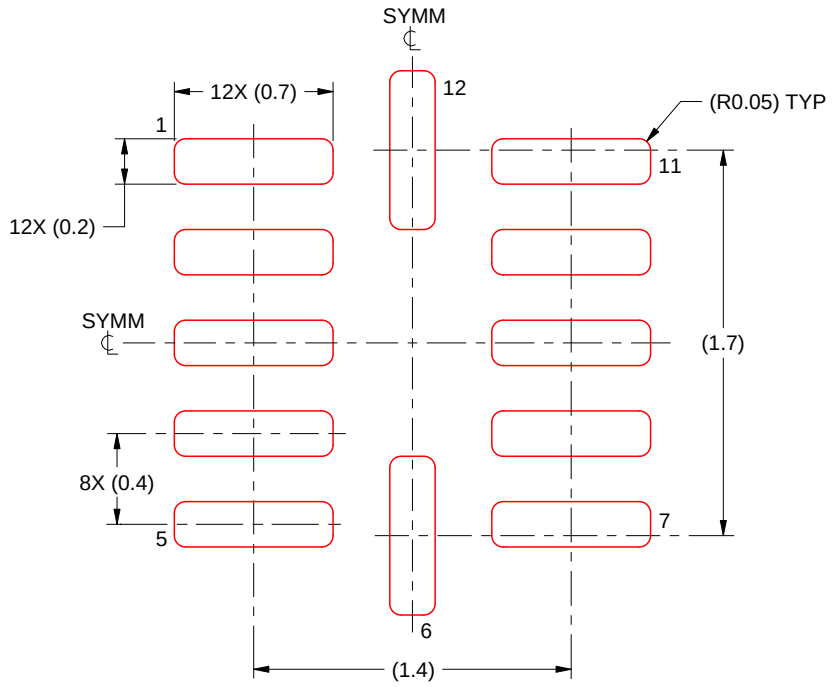


SOLDER MASK DETAILS

4220310/A 11/2016

NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE: 30X

4220310/A 11/2016

NOTES: (continued)

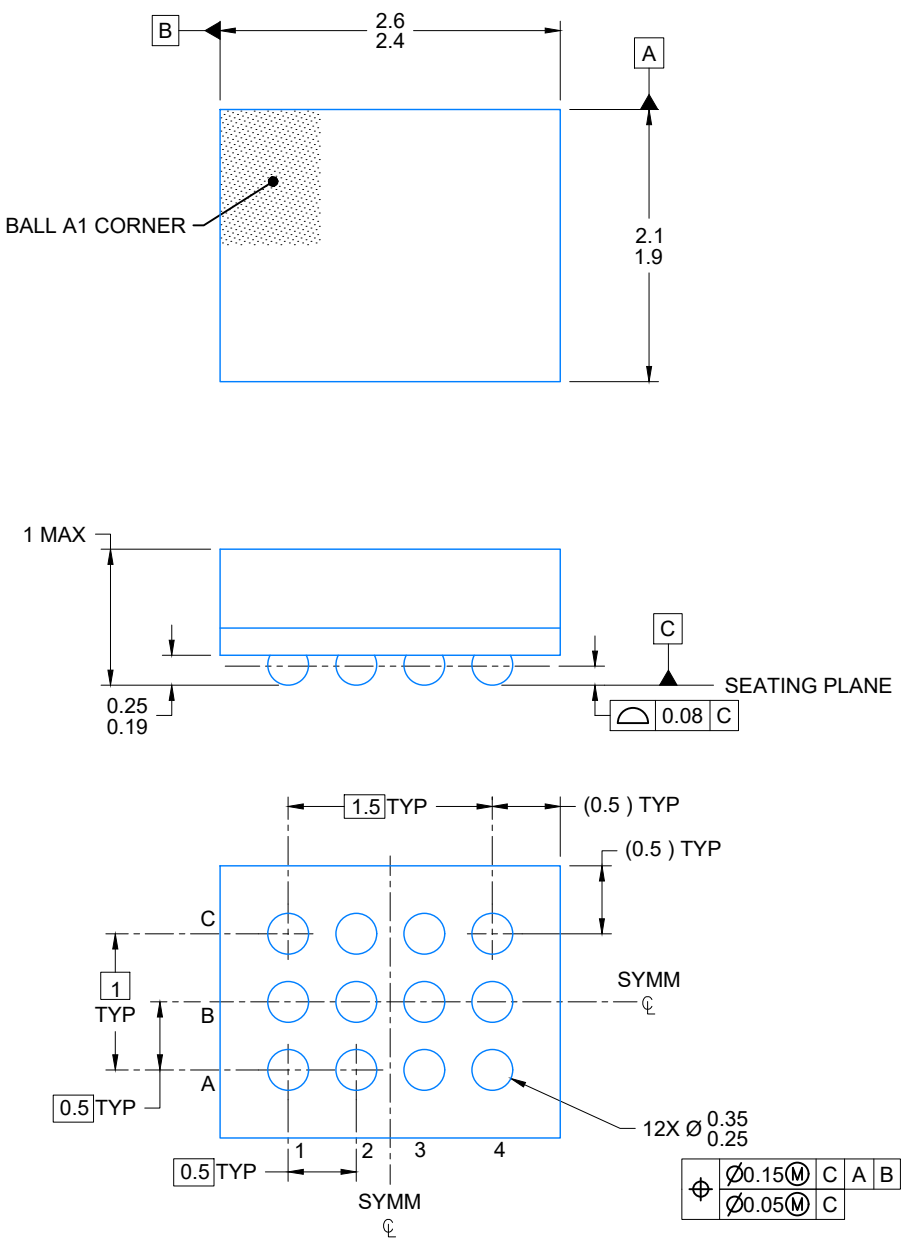
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

NMN0012A

NFBGA - 1 mm max height

PLASTIC BALL GRID ARRAY

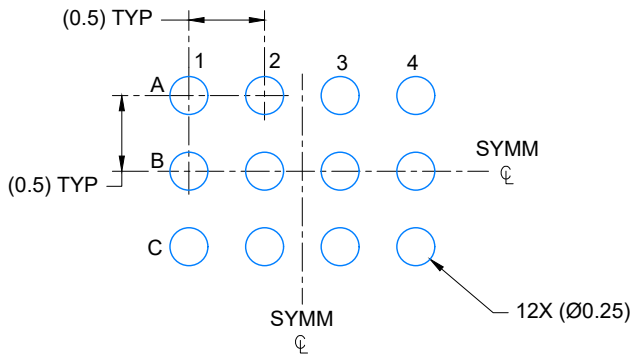


4225768/A 03/2020

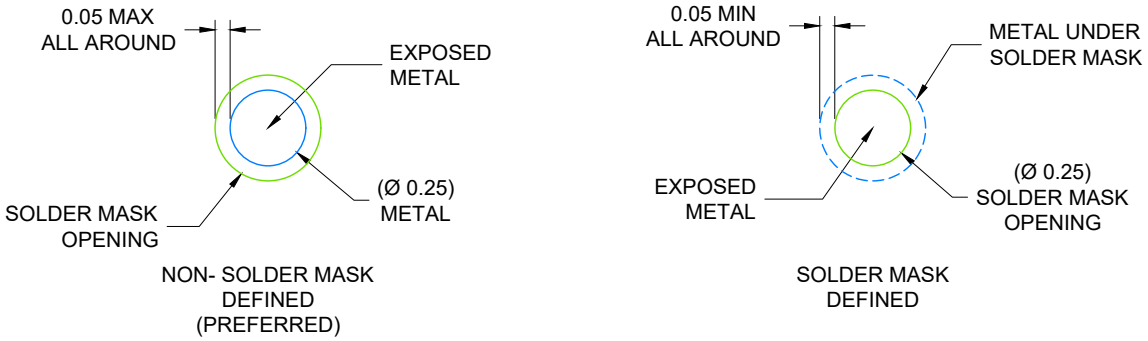
NOTES:

NanoFree is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE: 20X

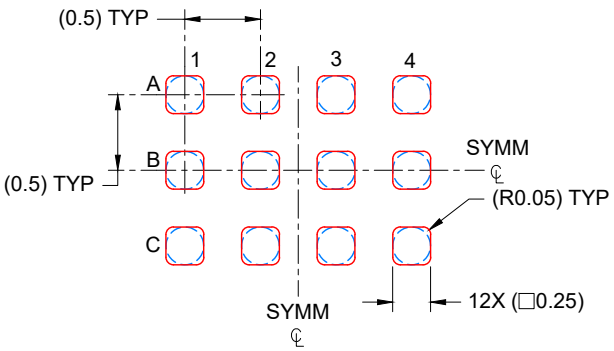


SOLDER MASK DETAILS
NOT TO SCALE

4225768/A 03/2020

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. Refer to Texas Instruments Literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.100 mm THICK STENCIL
SCALE: 20X

4225768/A 03/2020

NOTES: (continued)

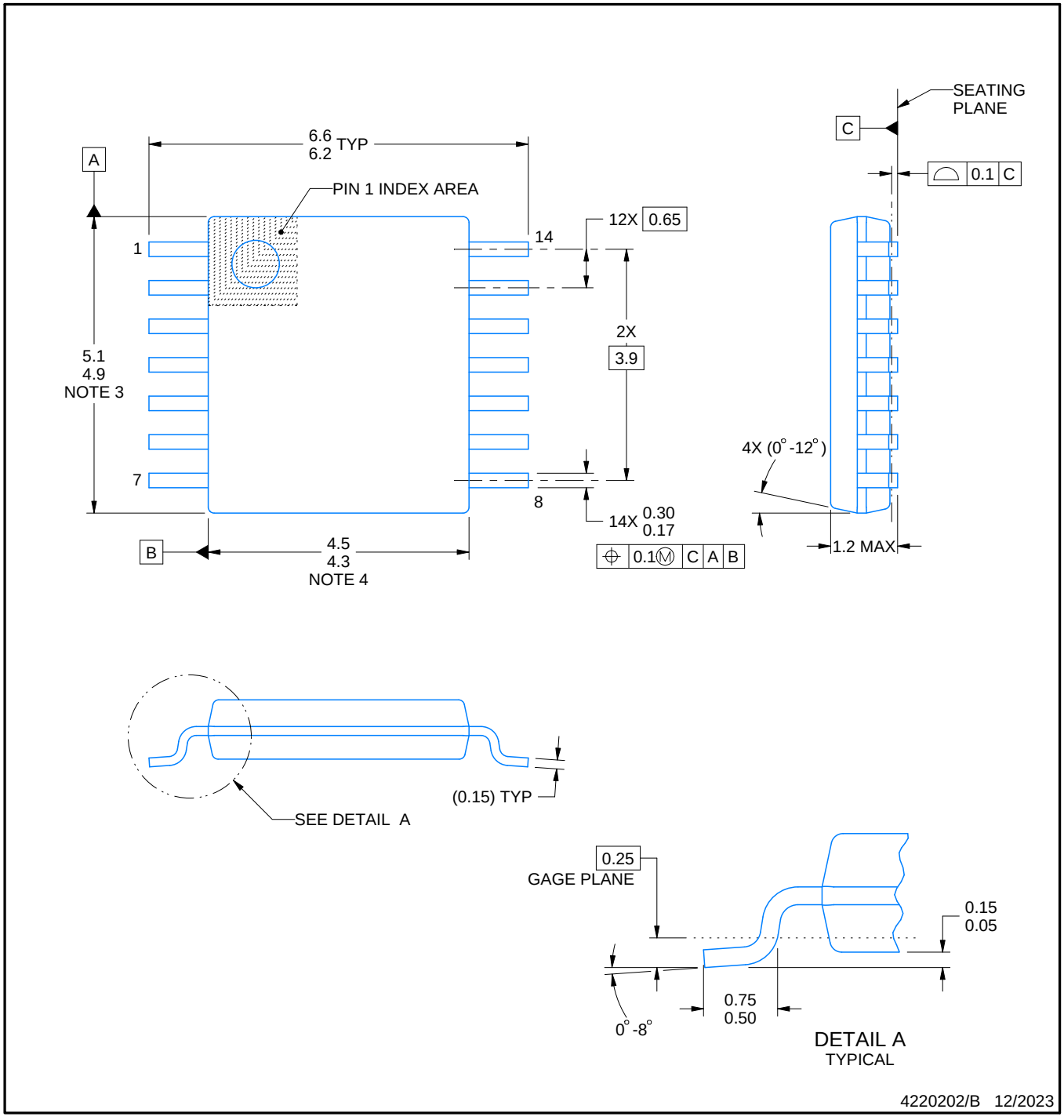
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

PACKAGE OUTLINE

PW0014A

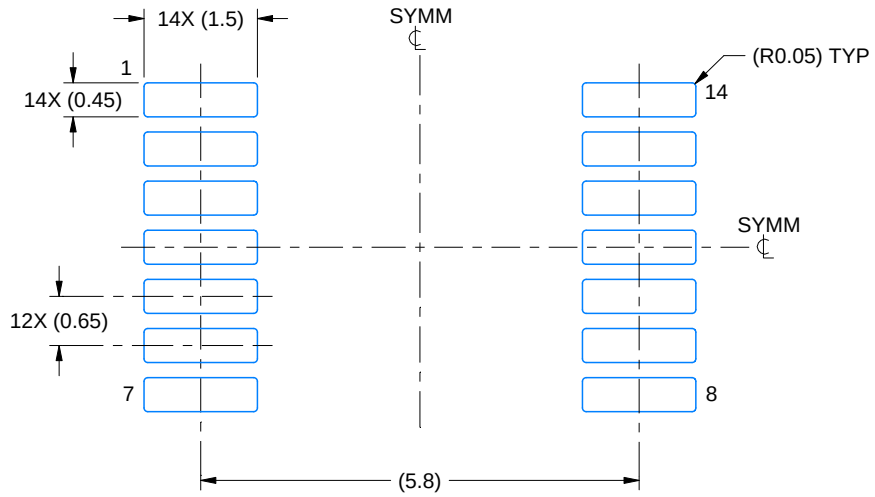
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

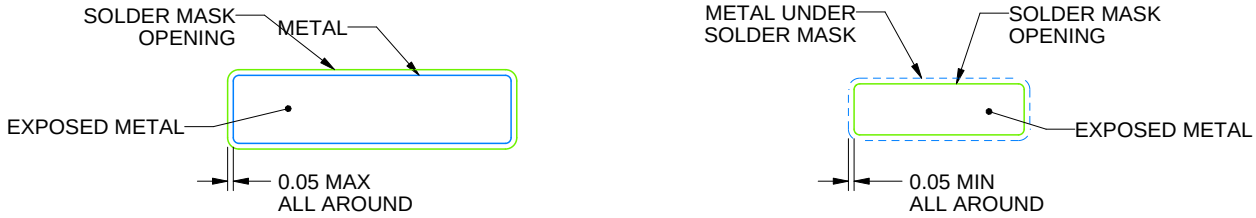


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

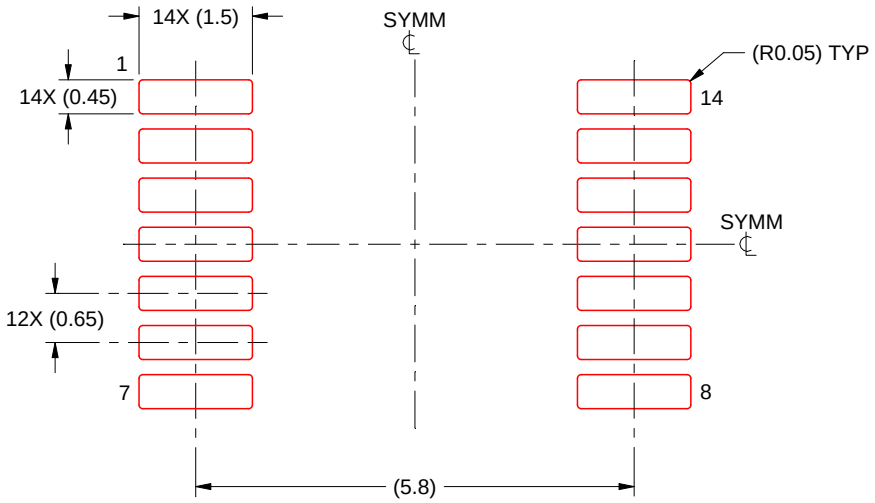


SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



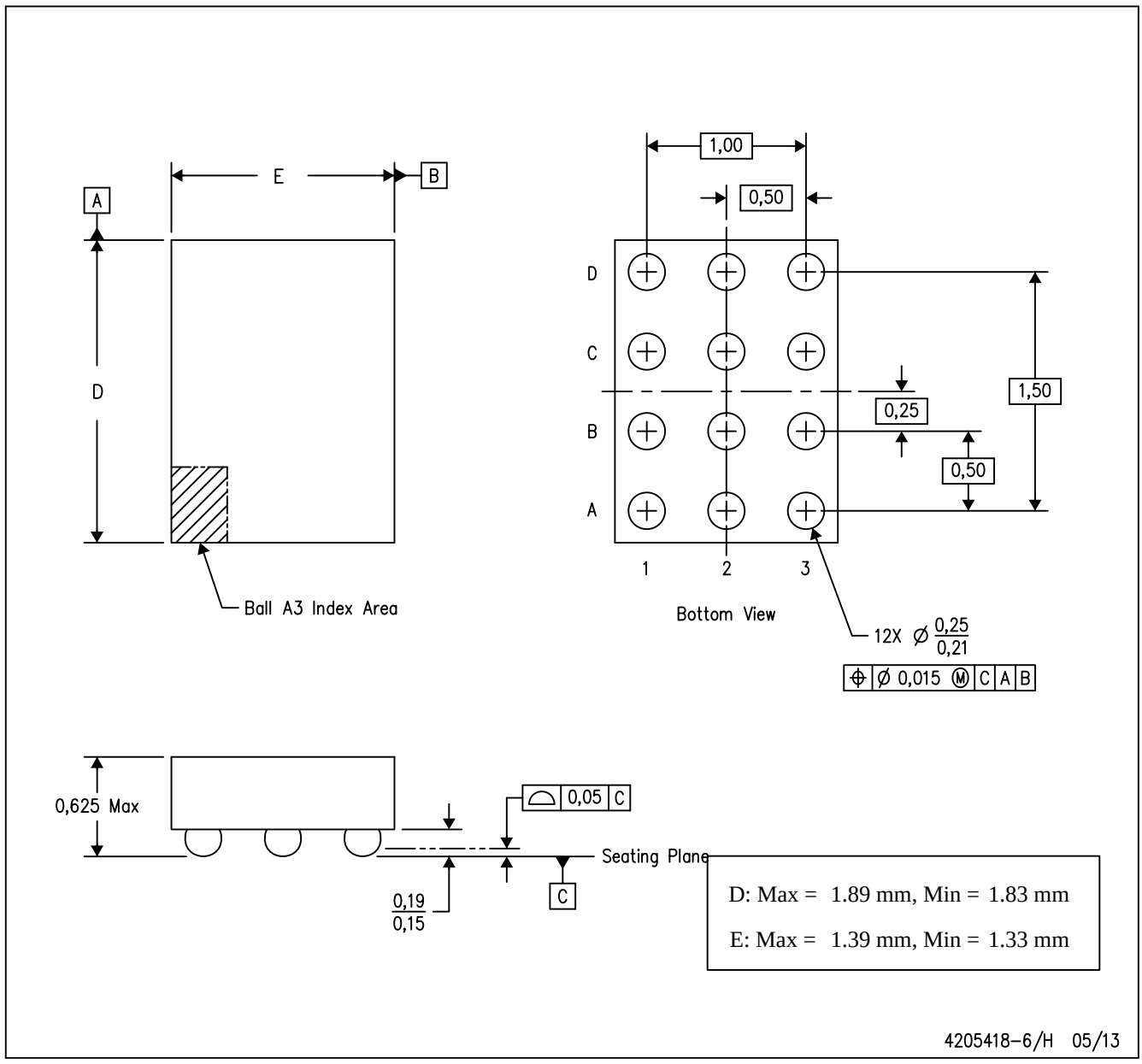
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

YZT (R–XBGA–N12) (CUSTOM) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

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